

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, emplo



FCMT299N60

N-Channel SuperFET® II MOSFET

600 V, 12 A, 299 mΩ

Features

- 650 V @ T_J = 150°C
- $R_{DS(on)} = 250 \text{ m}\Omega \text{ (Typ.)}$
- Ultra Low Gate Charge (Typ. Q_g = 39 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 127 pF)
- 100% Avalanche Tested
- · RoHS Compliant

Applications

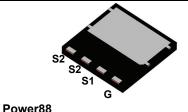
- · Server and Telecom Power Supplies
- · Solar Inverters
- · Adaptors

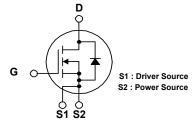
Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as server/telecom power, adaptor and solar inverter applications.

The Power88 package is an ultra-slim surface-mount package (1 mm high) with a low profile and small footprint (8x8 mm²). SuperFET II MOSFET in a Power88 package offers excellent switching performance due to lower parasitic source inductance and separated power and drive sources. Power88 offers Moisture Sensitivity Level 1 (MSL 1).







Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FCMT299N60	Unit
V _{DSS}	Drain to Source Voltage			600	V
\ /	Coto to Course Valtage	-DC		±20	
V_{GSS}	Gate to Source Voltage	-AC	(f > 1 Hz)	±30	_ V
	Drain Current	-Continuous (T _C = 25°C)		12	^
I _D	Drain Current	-Continuous (T _C = 100°C)		7.9	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	36	Α
E _{AS}	Single Pulsed Avalanche Ene	rgy	(Note 2)	234	mJ
I _{AR}	Avalanche Current		(Note 1)	2.5	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	1.25	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	20	V/ns
dv/dt	MOSFET dv/dt			100	V/ns
D	Dawar Dissipation	$(T_C = 25^{\circ}C)$		125	W
P_{D}	Power Dissipation	- Derate above 25°C		1	W/°C
T _J , T _{STG}	Operating and Storage Tempe	erature Range		-55 to +150	°C
Tı	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5 S	Seconds	300	οС

Thermal Characteristics

Symbol	Parameter	FCMT299N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (* 1 in² pad of 2 oz copper), Max.	45	*C/VV

Unit

Max.

Package Marking and Ordering Information

	Device Marking	Device	Package	Reel Size	Tape Width	Quantity
ſ	FCMT299N60	FCMT299N60	Power88	-	-	3000

Test Conditions

Min.

Тур.

Electrical Characteristics T_C = 25°C unless otherwise noted. **Parameter**

Off Characteristics						
D\/	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_C = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS}	Drain to Source Breakdown voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_C = 150^{\circ}\text{C}$	650	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	-	0.67	-	V/°C
ı	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	
DSS	Zero Gate Voltage Drain Gurrent	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	1.2	-	μA
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

Symbol

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	1	3.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	-	0.25	0.299	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 6 \text{ A}$	-	12	ı	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 200 V V - 0 V	-	1465	1948	pF
Coss	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V f = 1 MHz	-	30	40	pF
C _{rss}	Reverse Transfer Capacitance	1 = 1 1/11/12	-	4.87	-	pF
Coss eff.	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	-	127	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 6 A	-	39	51	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	6	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	14	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	8.0	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	19	48	ns
t _r		$V_{DD} = 380 \text{ V}, I_{D} = 6 \text{ A}$	-	9	28	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_g = 4.7 Ω	-	51	112	ns
t _f	Turn-Off Fall Time	(Note 4)	-	7	24	ns

Drain-Source Diode Characteristics

IS	Maximum Continuous Drain to Source Diode Forward Current			-	12	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	36	Α
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 6 \text{ A}$	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 6 A	-	262	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	3.8	-	μC

- **Notes:**1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. I_{AS} = 2.5A, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 3. $I_{SD} \le 6A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BVDSS$, Starting T_J = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

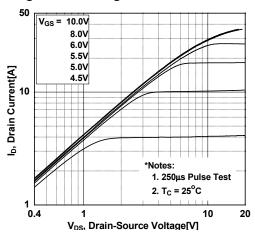


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

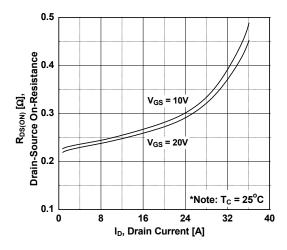


Figure 5. Capacitance Characteristics

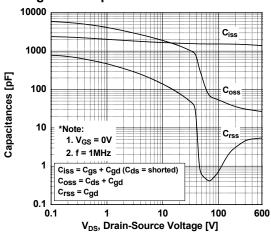


Figure 2. Transfer Characteristics

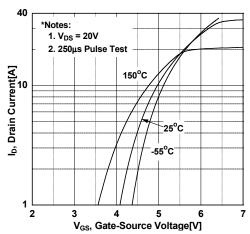


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

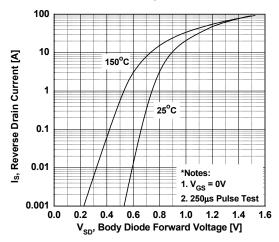
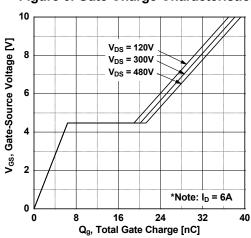


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

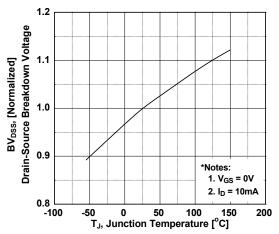


Figure 9. Maximum Safe Operating Area

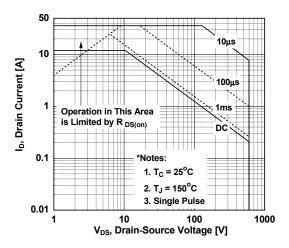


Figure 11. Eoss vs. Drain to Source Voltage

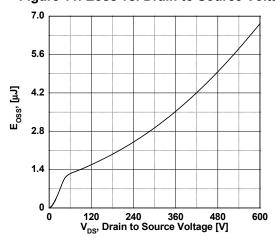


Figure 8. On-Resistance Variation vs. Temperature

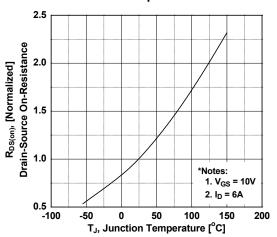
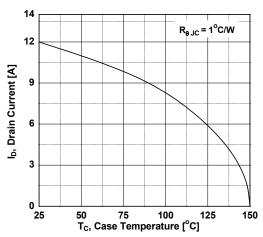
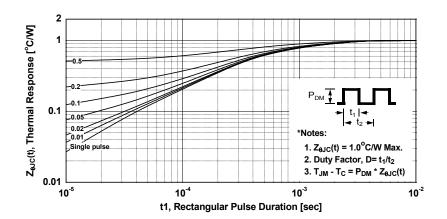


Figure 10. Maximum Drain Current vs. Case Temperature

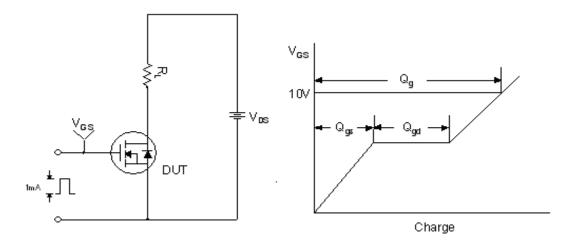


Typical Performance Characteristics (Continued)

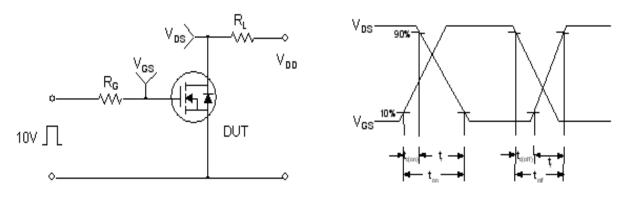




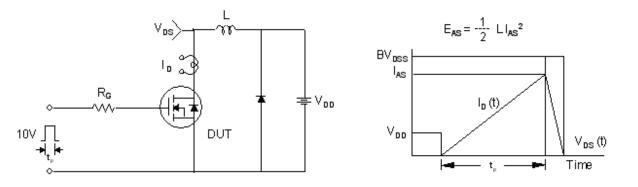
Gate Charge Test Circuit & Waveform



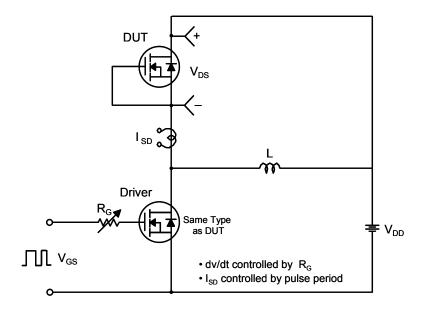
Resistive Switching Test Circuit & Waveforms

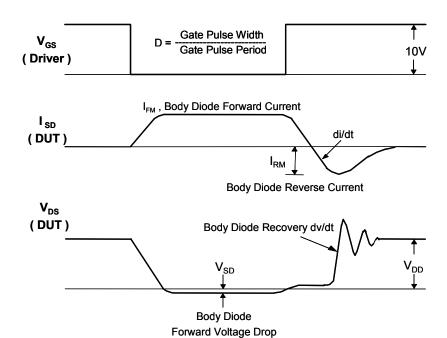


Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms





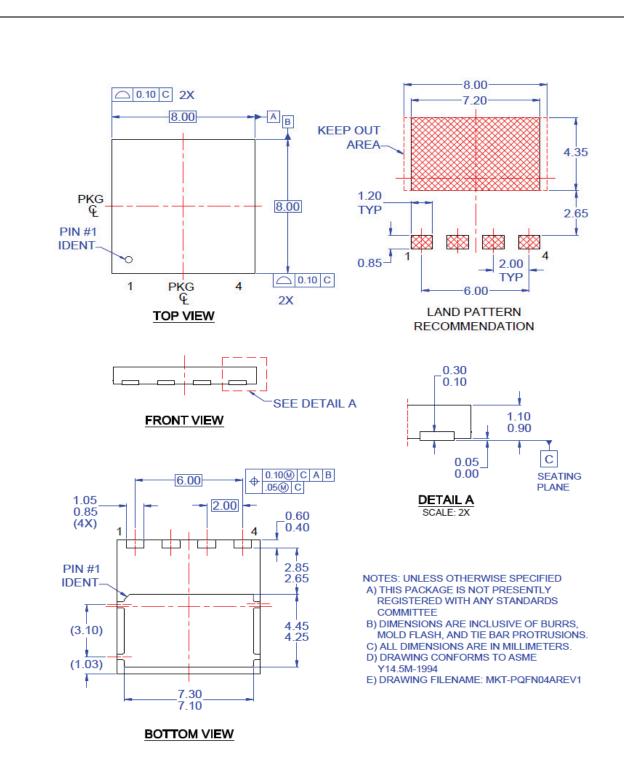


Figure 17. Molded Package, Power88, 4 Lead

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_PQBKR-004





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ F-PFS™ Awinda[®] AX-CAP®* BitSiC™ Build it Now™ CorePLUS™ CorePOWER™ CROSSVOLT™ CTL™

Current Transfer Logic™ DEUXPEED

Dual Cool™ EcoSPARK® EfficentMax™ ESBC™

Fairchild® Fairchild Semiconductor® FACT Quiet Series™

FACT[®] FAST® FastvCore™ FETBench™ FPS™

FRFET® Global Power ResourceSM GreenBridge™ Green FPS™

Green FPS™ e-Series™ Gmax™ GTO™ IntelliMAX™

ISOPLANAR™ Marking Small Speakers Sound Louder and Better™

MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ $MillerDrive^{TM}$ MotionMax™ $MotionGrid^{\circledR}$

MTi[®] MTx® MVN® mWSaver® OptoHiT™

(1)_® PowerTrench® PowerXS™

Programmable Active Droop™

OFFT QS™ Quiet Series™ RapidConfigure[™]

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™ SPM[®]

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™ Sync-Lock™

SYSTEM ®* TinyBoost[®] TinyBuck[®] TinyCalc™ TinyLogic[®] TIŃYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®* μSerDes™

UHC® Ultra FRFET™ UniFET™ VCX™ VisualMax™ VoltagePlus™ XS™ Xsens™ ? ? TM

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT http://www.fairchildsemi.com. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
		Pey 171

FCMT299N60 Rev. C0 9 www.fairchildsemi.com

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative